IN THE CLAIMS:

Claim 1 (canceled)

Claim 2 (currently amended) ~~The~~ A semiconductor device ~~as claimed in claim 1~~ comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line; and

a condenser chip in which a noise reduction condenser connected to said circuit block is formed,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein a plurality of circuit blocks are formed in said semiconductor chip, and said condenser chip has a plurality of condensers corresponding to said circuit blocks.

Claim 3 (currently amended) ~~The~~ A semiconductor device ~~as claimed in claim 1~~ comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line; and

a condenser chip in which a noise reduction condenser connected to said circuit block is formed,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein a plurality of circuit blocks are formed in said semiconductor chip, and a plurality of said condenser chips are provided corresponding to said circuit blocks.

Claim 4 (currently amended) ~~The~~ semiconductor device ~~as claimed in claims 1~~ comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line; and

a condenser chip in which a noise reduction condenser connected to said circuit block is formed,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein said semiconductor chip has a first power supply pad provided on a connecting line extending from one of said power supply line and said ground line to said circuit block; and

said condenser chip has a second electrode pad connected to the condenser, and the second electrode pad of said condenser chip is electrically connected to the first electrode pad of said semiconductor chip through a bonding wire.

Claim 5 (currently amended) ~~The~~ A semiconductor device ~~as claimed in claims 1~~ comprising:

a semiconductor chip having a circuit block, a power supply line and a ground line; and

a condenser chip in which a noise reduction condenser connected to said circuit block is formed,

wherein said condenser chip is stacked on said semiconductor chip, and

wherein said semiconductor chip has a first power supply pad provided on a connecting line extending from one of said power supply line and said ground line to said circuit block; and

said condenser chip has a second electrode pad connected to the condenser, and said

condenser chip is connected to the first electrode pad of said semiconductor chip by flip chip bonding.

Claim 6 (currently amended) The semiconductor device as claimed in ~~claims 1~~ claim 2, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

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Claim 7 (currently amended) The semiconductor device as claimed in ~~claims 1~~ claim 4, wherein said semiconductor chip has a third electrode pad other than said first electrode pad connected to said circuit block;

said condenser chip has a fourth electrode pad other than said second electrode pad connected to the condenser; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said fourth electrode pad of said condenser chip and said third electrode pad of said semiconductor chip by a bonding wire.

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Claim 8 (original) The semiconductor device as claimed in claim 7, wherein a plurality of said fourth electrode pads of said condenser chip are provided and a plurality of said third electrode pads of said semiconductor chip are provided; and

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said inductor is formed by alternately and sequentially connecting said fourth electrode pads of said condenser chip and said third electrode pads of said semiconductor chip by bonding wires.

Claim 9 (original) A semiconductor device comprising: a first semiconductor chip having a circuit block, a power supply line and a ground line; and a second semiconductor chip stacked on said first semiconductor chip, wherein said first semiconductor chip has a first electrode pad separated from a circuit formed within said first semiconductor chip;

said second semiconductor chip has a second electrode pad separated from a circuit formed within said second semiconductor chip; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said first electrode pad of said first semiconductor chip and said second electrode pad of said second semiconductor chip by a bonding wire.

Claim 10 (original) The semiconductor device as claimed in claim 9, wherein a plurality of said first electrode pads of said first semiconductor chip are provided and a plurality of said second electrode pads of said second semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said first electrode pads of said first semiconductor chip and said second electrode pads of said second semiconductor chip by bonding wires.

Claim 11 (new) The semiconductor device as claimed in claim 2,

wherein said power supply line and said grounding line have a ring shaped configuration, respectively,

a plurality of circuit blocks are formed inside said ring shaped power supply line and

grounding line, and

said circuit block is connected to said condenser chip on a connecting line extending from one of said ring shaped power supply line and grounding line to said circuit block.

Claim 12 (new) The semiconductor device as claimed in claim 3,

wherein said power supply line and said grounding line have a ring shaped configuration, respectively,

a plurality of circuit blocks are formed inside said ring shaped power supply line and grounding line, and

said circuit block is connected to said condenser chip on a connecting line extending from one of said ring shaped power supply line and grounding line to said circuit block.

Claim 13 (new) The semiconductor device as claimed in claim 3, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

Claim 14 (new) The semiconductor device as claimed in claim 4, wherein the noise reduction condenser of said condenser chip is formed by a MOS capacity.

Claim 15 (new) The semiconductor device as claimed in claim 5, wherein the noise reduction condenser of said condenser of said condenser chip is formed by a MOS capacity.

Claim 16 (new) The semiconductor device as claimed in claim 5,

wherein said semiconductor chip has a third electrode pad other than said first electrode pad connected to said circuit block;

said condenser chip has a fourth electrode pad other than said second electrode pad connected to the condenser; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said fourth electrode pad of said condenser chip and said third electrode pad of said semiconductor chip by a bonding wire.

Claim 17 (new) The semiconductor device as claimed in claim 16,

wherein a plurality of said fourth electrode pads of said condenser chip are provided and a plurality of said third electrode pads of said semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said fourth electrode pads of said condenser chip and said third electrode pads of said semiconductor chip by bonding wires.